- The diffusion constant for holes in 8i is $13 \text{ cm}^2/\text{sec}$. What is diffusion current density if got gradient of hole conventuation, $\frac{dP}{dx} = -2 \times 10^{14} \text{ holes } / \text{cm}^2.$ Ans $\rightarrow -0.416 \text{ mA } / \text{cm}^2$
- ② Calculate the factor by which reverse saturation current of diode is multiplied when temperature increases from 25°C to 80°C.

 ANS → 45.25
- B) A Gre projunction diode is operating at a temperature of 125°C with saturation current of 30MA. Calculate the objinance resistance when it is biased by a bias voltage of 0.2V In forward direction.

 Are > 3.366 \(\Omega \).
- (4) Calculate having transition capacitance of a Ge diode whose area is 1 mm × 1 mm and space charge thickness is 2×10^{-4} cm and 2n = 16. Ans $\rightarrow 70.832$ gf.
- (3) If a pure si regulal has I million free e's inside it, how many holes does it have? The > 1 million
- © Given n°; for si at $300 \, \text{k}$ is $1.5 \times 10^{10} \, \text{cm}^3$, $\mu_n = 1300 \, \text{cm}^2/\text{vs}$, $\mu_p = 500 \, \text{cm}^2/\text{vs}$
 - (i) Find interinsic conductivity Ans 4.32 × 106 S/an
 - (ii) Find no. of holes if no. of electrons are 5×1014
 - (iii) And resistivity of conductivity is 0.0224 s/cm Ans > 44.64 Scm

- Find the no. of holes and electrons in ntype si it conductivity is 300 s/cm. Given that for or at 300k, $n_i = 1.5 \times 10^{10}/\text{cm}^3$ $M_N = 1300 \text{ cm}^2/\text{VS}$ and $M_P = 500 \text{ cm}^2/\text{VS}$ As \Rightarrow 1.442 × 10¹⁸ cm², 1.56 × 10² cm⁻³
- (8) when a RBS reverse lies is applied to be, the reverse saturation current is 0.3 MA. Actumine current flowing in diode when 0.15 V forward lies is applied at room temp? Ares 120.73 MA
- The diode current is 0.6 mA when applied rollage is 400 mV and 20 mA when applied voltage is 500 mV. Actumine M.

 Assume $\frac{u\tau}{q} = 25 \text{mV}$. And $\rightarrow 1.14$
- @ Attention forward resistance of a pn junction diale when the forward current is 5 mA at T=300k. Assume. Si Ahr > 10.34.2
- The voltage across a 2° diode at noom temp? (300k) is 0.70 when 2 mA current flows through it. If voltage increases to 0.75 V, calculate the diode current (Assume VI = 26mV) Ares > 5.23 V mA (O1) 5.43 mA
- (2) A si diale has a saturation current of 7.5 MA at room temp?

 Calculate the saturation current at 400h. Ans > 7.68 mA
- 13) The reverse saturation current of the diode is 2MA at room temp? of 25°C. Find the reverse saturation current at 75°C. Ares > 64MA.
- (4) A transistor has P = 100. If collector current is 40 mA. Find the value of emitter current. Aus > 40.4 mA
- (5) If B= 150 then find collector and have current, if IE=10mA

 AND > 9.93 mA, 0.07 mA

- (16). For a teansister, $\alpha = 0.98$, IcBo = Ico = 5UA and IB = 100MA.

 And Ic and IE Ans > 5.15 mA, 5.25 mA
 - (F) Corlendate the values of Ic and IE for a transistor with d = 0.99, ICBO = 5UA, IB = 20UA ANS > 2.45MA, 2.5MA.
- (8) Retermine leave, collector and smither current and VCE for CE circuit of VCC = 10V, VBB = 4V, RB = 200 = 200 PC , RC = 2kr VBE(ON) = 0.7V, B = 200

F CIRCLE of VCC = 10 VBE(ON) = 0.7V, B = 200 Ans > 16.5 MA, 3.3 mA, RB TO NBB TB > 16.5 MA, 3.4N

and Ico = 0.0 mA. What current will flow in collector circuit of transister when connected in CE configuration with Is 30 MA.

ANS -> 3.97 mA

Region Retermine VCEB and ICB.

VBB=5V RB=ROKE

VCEB = 4.634V

ICB = 5.334mA VCEB = 4.634V VCEB = 4.634V VCEB = 5.334mA

- (2) Find collecter current and VCE for fixed lias with VBE = 0.7V,

 RB = 300 USL, RC = 2 USL, B = 50, VCC = 9V Ans > 1.38mA

 Find stability factor.

 6.24 V
- A few transister has P = 100 and VBE = 0.2 V in fixed lives amplifier circuit when VCC = 16 V, $RB = 790 \, \text{ks}$. Determine its operating point if $RC = 5 \, \text{ks}$. If $RC = 5 \, \text{ks}$.
- RE = 1 ks, P=50 Find stability factor and VCE.

 Ans > 43.04, 6.38V

27 68 -> X2 ANS -> 010 111 110

62 110110101012 -> X8 -> ANS -> 33258

20 4448 > X10 Ans -> 29210

27 1208 -> X10 ANS -> 8010

(38) 23F16 -> X10 Ans > 575

29 2A16 -> X2 ANS > 001010100110

30 2416 -> X8 ANS -> 0448

31) 248 -> X16 Am -> 14

32 110/110.10/112 > X16 Ams > 6E.B816

33 73.375,0 > X8 Am >111.308

(34) 376₁₀ >> × 16 Ars -> 17816

(35) Construct a full subtractor using half subtractor and OR gates. Ans > 2Hs + 1 OR gate

(36) For a BJT, $\lambda = 0.98$, $I_{co} = 0.6MA$. This BJT is connected in CE mode and operating in active region with $I_B = 20 \mu A$ Find Ic. Ans > 1:01 mA

(37) The reverse saturation current of collector lease junction That ILBO = 10 nA when d = 0.98. Find ICEO. AND > 0.5MA.

(38) A transistor has sevent gain of 0.99 in CB. Find its current gain in (c. Ans > 100